

Fast Recovery Avalanche Diode Type DFA233-200-15

Low switching losses
Low reverse recovery charge
High power cycling capability

Average forward current		I_{FAV}	200 A
Repetitive peak reverse voltage		V_{RRM}	1300...1500 V
Reverse recovery time		t_{rr}	1.25, 1.60, 2.00, 2.50 μ s
V_{RRM} , V	1300	1400	1500
Voltage code	13	14	15
T_j , °C	-60...+125		

MAXIMUM ALLOWABLE RATINGS

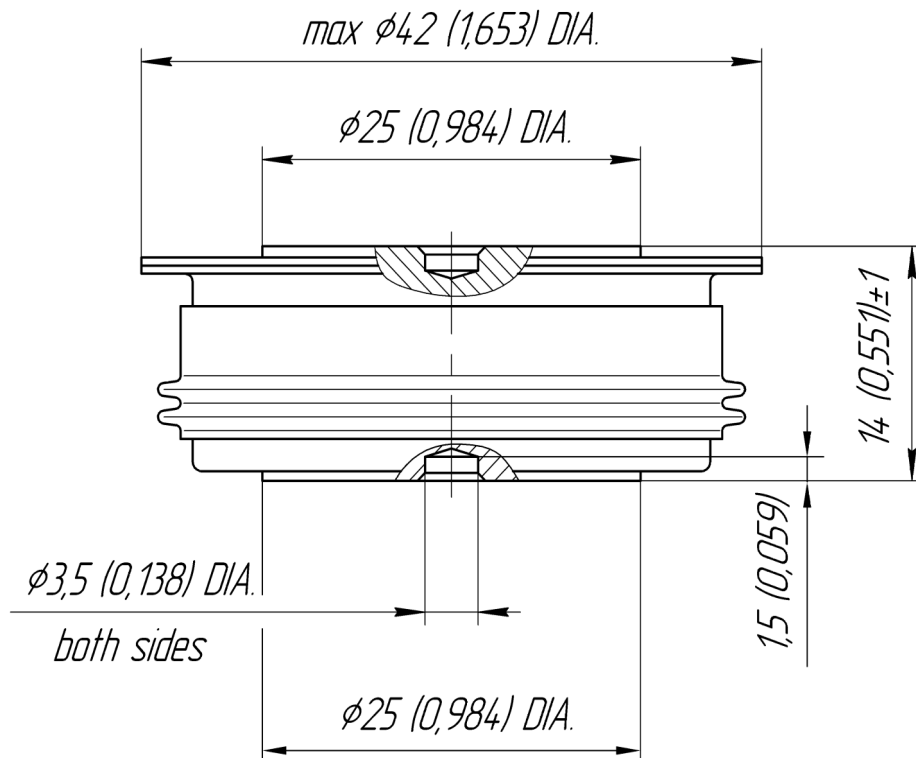
Symbols and parameters		Units	Values	Test conditions
ON-STATE				
I_{FAV}	Average forward current	A	200	$T_c=90$ °C; Double side cooled; 180° half-sine wave; 50 Hz
I_{FRMS}	RMS forward current	A	314	$T_c=90$ °C; Double side cooled; 180° half-sine wave; 50 Hz
I_{FSM}	Surge forward current	kA	4.8 5.5	$T_j=T_{j\max}$ $T_j=25$ °C 180° half-sine wave; $t_p=10$ ms; single pulse; $V_R=0$ V;
			5.0 6.0	$T_j=T_{j\max}$ $T_j=25$ °C 180° half-sine wave; $t_p=8.3$ ms; single pulse; $V_R=0$ V;
I^2t	Safety factor	$A^2s \cdot 10^3$	110 150	$T_j=T_{j\max}$ $T_j=25$ °C 180° half-sine wave; $t_p=10$ ms; single pulse; $V_R=0$ V;
			100 140	$T_j=T_{j\max}$ $T_j=25$ °C 180° half-sine wave; $t_p=8.3$ ms; single pulse; $V_R=0$ V;
BLOCKING				
V_{RRM}	Repetitive peak reverse voltages	V	1300...1500	$T_{j\min} < T_j < T_{j\max}$; 180° half-sine wave; 50 Hz;
V_{RSM}	Non-repetitive peak reverse voltages	V	1400...1600	$T_{j\min} < T_j < T_{j\max}$; 180° half-sine wave; single pulse;
$V_{(BR)}$	Breakdown voltage	V	1500...1700	$T_j=25$ °C; $I_{br}=100$ mA; $t_p = 10$ ms; 5 Hz
V_R	Reverse continuous voltages	V	$0.6 \cdot V_{RRM}$	$T_j=T_{j\max}$;
P_{RSM}	Surge reverse power dissipation	kW	16	$T_j= T_{j\max}$; $t_p = 100$ μ s; 180° half-sine current waveforms; single pulse
THERMAL				
T_{stg}	Storage temperature	°C	-60...+55	
T_j	Operating junction temperature	°C	-60...+125	
MECHANICAL				
F	Mounting force	kN	9.0...11.0	
a	Acceleration	m/s ²	50	Device clamped

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions
ON-STATE				
V_{FM}	Peak forward voltage, max	V	3.50	$T_j=25\text{ }^\circ\text{C}; I_{FM}=628\text{ A}$
$V_{F(TO)}$	Forward threshold voltage, max	V	1.10	$T_j=T_{j\text{ max}};$
r_T	Forward slope resistance, max	m Ω	6.70	$0.5\pi I_{FAV} < I_T < 1.5\pi I_{FAV}$
BLOCKING				
I_{RRM}	Repetitive peak reverse current, max	mA	40	$T_j=T_{j\text{ max}};$ $V_R=V_{RRM}$
SWITCHING				
Q_{rr}	Total recovered charge, max	μC	tbd*	$T_j=T_{j\text{ max}}; I_{FM}=I_{FAV};$ $di_R/dt=-100\text{ A}/\mu\text{S};$ $V_R=100\text{ V};$
t_{rr}	Reverse recovery time ¹⁾ , max	μS	1.25, 1.60, 2.00, 2.50	
I_{rrM}	Peak reverse recovery current, max	A	tbd*	
THERMAL				
R_{thjc}	Thermal resistance, junction to case, max	$^\circ\text{C}/\text{W}$	0.040	Double side cooled
R_{thjc-A}			0.088	Direct current Anode side cooled
R_{thjc-K}			0.072	Cathode side cooled
R_{thck}	Thermal resistance, case to heatsink, max	$^\circ\text{C}/\text{W}$	0.009	Direct current
MECHANICAL				
w	Weight, max	g	90	
D_s	Surface creepage distance	mm (inch)	11.10 (0.437)	
D_a	Air strike distance	mm (inch)	11.60 (0.457)	

* **tbd** – data will be refined as additional tests are conducted and statistics are collected.

PART NUMBERING GUIDE						NOTES										
DFA	233	200	15	M4	N	¹⁾ Reverse recovery time <table border="1" style="margin-left: 20px;"> <thead> <tr> <th>Symbol of group</th> <th>X4</th> <th>T4</th> <th>P4</th> <th>M4</th> </tr> </thead> <tbody> <tr> <td>$t_{rr}, \mu\text{S}$</td> <td>1.25</td> <td>1.60</td> <td>2.00</td> <td>2.50</td> </tr> </tbody> </table>	Symbol of group	X4	T4	P4	M4	$t_{rr}, \mu\text{S}$	1.25	1.60	2.00	2.50
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$t_{rr}, \mu\text{S}$	1.25	1.60	2.00	2.50												
1	2	3	4	5	6											
1. DFA – Fast recovery avalanche diode 2. Design version 3. Average forward current, A 4. Voltage code 5. Group of reverse recovery time 6. Ambient conditions: N – normal; T – tropical																



All dimensions in millimeters (inches)